



Arab Academy for Science & Technology & Maritime Transport
(AASTMT – Cairo Branch)
College of Engineering & technology
Electronics & Communication Engineering Department

Course : Solid State Electronics
Course Code : EC210

Sheet #4

TextBook

‘Principles of Electronic Materials and Devices’, Third Edition, S.O. Kasap © McGraw-Hill, 2006

Constants:

$$\epsilon_0 = 8.85 \times 10^{-12} \text{ Fm}^{-1}$$

$$\text{Charge of electron (q)} = 1.6 \times 10^{-19} \text{ C}$$

$$\text{Mass of electron (m}_e\text{)} = 9.1 \times 10^{-31} \text{ kg}$$

$$\text{Plank's Constant (h)} = 6.63 \times 10^{-34} \text{ Js}$$

Solve the following problems

- [1] Find the resistivity of intrinsic Germanium (Ge) at 300K where $\mu_n = 3800 \text{ cm}^2/\text{V}\cdot\text{sec}$, $\mu_p = 1800 \text{ cm}^2/\text{V}\cdot\text{sec}$ and intrinsic concentration $1.6 \times 10^{13} \text{ cm}^{-3}$.
- [2] For intrinsic silicon at room temperature, given that the intrinsic concentration is $1 \times 10^{10} \text{ cm}^{-3}$, the mean time between scatterings is $2 \times 10^{-13} \text{ sec}$ for electrons, and $1 \times 10^{-13} \text{ sec}$ for holes, the conductivity effective mass for electrons is $0.26m_0$, and $0.386m_0$ for holes, where m_0 is the rest mass for the electrons.
Find:
a. Electron and hole mobilities
b. Total conductivity.
c. The current density if the silicon has a length of $1 \mu\text{m}$, and an applied voltage of 10V .
d. The total current if the cross section area is $100 \mu\text{m}^2$.
Hint: use MKS system
- [3] Example 5.3 p.392.
- [4] An intrinsic semiconductor with $L=10 \mu\text{m}$. The potential $V(x)$ applied is given as:
$$\frac{-2}{10 \times 10^{-6}} x + 2$$
. Plot both $V(x)$ and the potential energy versus x .
- [5] For an electron mobility of $500 \text{ cm}^2/\text{V}\cdot\text{sec}$, calculate the time between collisions, for an electric field of 100 V/cm , calculate also the distance traveled by an electron between collisions. Take $m^* = m$ in this calculation.
- [6] For a p-type silicon slice doped with Boron (Acceptor, N_A). The doping gradient have a linear dependence on distance, with $N_A(\text{at } x=0 \mu\text{m}) = 5 \times 10^{16} \text{ cm}^{-3}$, and $N_A(\text{at } x=100 \mu\text{m}) = 10^{17} \text{ cm}^{-3}$. Given that the cross section area = $10 \mu\text{m}^2$, length= $100 \mu\text{m}$, mobility = $600 \text{ cm}^2/\text{V}\cdot\text{sec}^{-1}$, temperature = 27°C , find the total diffusion current.
Note: Use $k= 1.3806488 \times 10^{-23} \text{ J}\cdot\text{K}^{-1}$.